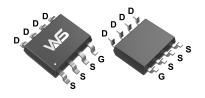




## **Features**

- 40V/11A,  $R_{DS(ON)} = 13m\Omega \text{ (Max.)} @ V_{GS} = 10V$  $R_{DS(ON)} = 16m\Omega \text{ (Max.)} @ V_{GS} = 4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

## **Pin Description**



Top View of SOP-8

# **Applications**

 Power Management in Desktop Computer or DC/DC Converters.



N-Channel MOSFET

## **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C Unless Otherwise Noted)

| Symbol                       | Parameter                              | Rating               | Unit |      |  |  |  |  |
|------------------------------|--|----------------------|------|------|--|--|--|--|
| Common Ratings               |  |                      |      |      |  |  |  |  |
| $V_{DSS}$                    | Drain-Source Voltage                   | 40                   | V    |      |  |  |  |  |
| $V_{GSS}$                    | Gate-Source Voltage                    | ±20                  |      |      |  |  |  |  |
| TJ                           | Maximum Junction Temperature           |                      | 150  | - °C |  |  |  |  |
| T <sub>STG</sub>             | Storage Temperature Range              | -55 to 150           | ] [  |      |  |  |  |  |
| Is                           | Diode Continuous Forward Current       | T <sub>A</sub> =25°C | 2    | Α    |  |  |  |  |
|                              | Continuous Drain Current               | T <sub>A</sub> =25°C | 11   |      |  |  |  |  |
| I <sub>D</sub>               |  | T <sub>A</sub> =70°C | 8.4  | Α    |  |  |  |  |
| I <sub>DM</sub> <sup>a</sup> | Pulsed Drain Current                   | T <sub>A</sub> =25°C | 30   |      |  |  |  |  |
| В                            | Maximum Power Dissipation              | T <sub>A</sub> =25°C | 2.08 | w    |  |  |  |  |
| P <sub>D</sub>               |  | T <sub>A</sub> =70°C | 1.3  | \\   |  |  |  |  |
| В                            | Thermal Resistance-Junction to Ambient | t ≤ 10s              | 30   |      |  |  |  |  |
| $R_{\theta JA}$              |  | Steady State         | 60   | °C/W |  |  |  |  |
| $R_{\theta JL}$              | Thermal Resistance-Junction to Lead    | Steady State         | 20   |      |  |  |  |  |
| I <sub>AS</sub> b            | Avalanche Current, Single pulse        | L=0.1mH              | 23   | Α    |  |  |  |  |
| E <sub>AS</sub> <sup>b</sup> | Avalanche Energy, Single pulse         | L=0.1mH              | 26   | mJ   |  |  |  |  |

Note a: Max. current is limited by bonding wire.

Note b: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T<sub>i</sub>=25°C).



# **Electrical Characteristics** (T<sub>A</sub> = 25°C Unless Otherwise Noted)

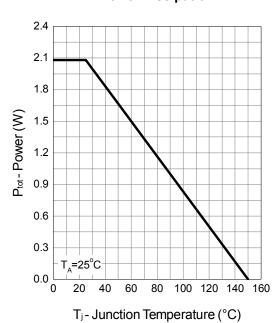
| Symbol                                 | Parameter                        | Test Conditions   | Min. | Тур.  | Max. | Unit |
|--|----------------------------------|---|------|-------|------|------|
| Static Ch                              | aracteristics                    |   | !    | ļ     |      |      |
| BV <sub>DSS</sub>                      | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA                         | 40   | -     | -    | V    |
| I <sub>DSS</sub>                       | Zero Gate Voltage Drain Current  | V <sub>DS</sub> =32V, V <sub>GS</sub> =0V                           | -    | -     | 1    | μА   |
|  |                                  | T <sub>J</sub> =85°C  | -    | -     | 30   |      |
| $V_{GS(th)}$                           | Gate Threshold Voltage           | $V_{DS}=V_{GS}$ , $I_{DS}=250\mu A$                                 | 1.5  | 1.8   | 2.5  | V    |
| I <sub>GSS</sub>                       | Gate Leakage Current             | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                          | -    | -     | ±100 | nA   |
|  |                                  | V <sub>GS</sub> =10V, I <sub>DS</sub> =7A                           | -    | 10.5  | 13   |      |
| $R_{\text{DS}(\text{ON})}^{}\text{c}}$ | Drain-Source On-state Resistance | T <sub>J</sub> =125°C   | -    | 15.75 | -    | mΩ   |
| L                                      |                                  | V <sub>GS</sub> =4.5V, I <sub>DS</sub> =5A                          | -    | 12    | 16   |      |
| Gfs                                    | Forward Transconductance         | V <sub>DS</sub> =5V, I <sub>DS</sub> =15A                           | -    | 31    | -    | S    |
| Diode Ch                               | aracteristics                    | •   |      |       |      |      |
| V <sub>SD</sub> <sup>c</sup>           | Diode Forward Voltage            | I <sub>SD</sub> =10A, V <sub>GS</sub> =0V                           | -    | 0.9   | 1.1  | V    |
| t <sub>rr</sub>                        | Reverse Recovery Time            |   | -    | 15.2  | -    | ns   |
| t <sub>a</sub>                         | Charge Time                      | $V_{DD}$ =20V,  | -    | 9.4   | -    |      |
| t <sub>b</sub>                         | Discharge Time                   | $I_{SD}$ =10A, $dI_{SD}/dt$ =100A/ $\mu$ s                          | -    | 5.8   | -    |      |
| $Q_{rr}$                               | Reverse Recovery Charge          |   | -    | 9.5   | -    | nC   |
| Dynamic                                | Characteristics <sup>d</sup>     |   |      |       |      |      |
| $R_{G}$                                | Gate Resistance                  | V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz                      | 0.7  | 1.1   | 1.8  | Ω    |
| C <sub>iss</sub>                       | Input Capacitance                | V <sub>GS</sub> =0V,  | -    | 1125  | -    | pF   |
| C <sub>oss</sub>                       | Output Capacitance               | $V_{DS}=20V$ ,  | -    | 132   | -    |      |
| C <sub>rss</sub>                       | Reverse Transfer Capacitance     | Frequency=1.0MHz  | -    | 70    | -    |      |
| t <sub>d(ON)</sub>                     | Turn-on Delay Time               |   | -    | 12.6  | -    |      |
| t <sub>r</sub>                         | Turn-on Rise Time                | $V_{DD}$ =20V, $R_L$ =20 $\Omega$ , $I_{DS}$ =1A, $V_{GEN}$ =10V,   | -    | 10    | -    | ns   |
| t <sub>d(OFF)</sub>                    | Turn-off Delay Time              | $R_{G}=1\Omega$   | -    | 23.6  | -    |      |
| t <sub>f</sub>                         | Turn-off Fall Time               |   | -    | 6     | -    |      |
| Gate Cha                               | rge Characteristics <sup>d</sup> |   |      | •     |      |      |
| $Q_g$                                  | Total Gate Charge                | V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V,<br>I <sub>DS</sub> =7A | -    | 9.4   | -    |      |
| Qg                                     | Total Gate Charge                |   | -    | 20    | 28   | nC   |
| $Q_{gth}$                              | Threshold Gate Charge            | V <sub>DS</sub> =20V, V <sub>GS</sub> =10V,                         | -    | 2     | -    |      |
| $Q_{gs}$                               | Gate-Source Charge               | I <sub>DS</sub> =7A   | -    | 3.9   | -    |      |
| $Q_{gd}$                               | Gate-Drain Charge                |   | _    | 3     | -    |      |

Note c : Pulse test ; pulse width≤300µs, duty cycle≤2%.

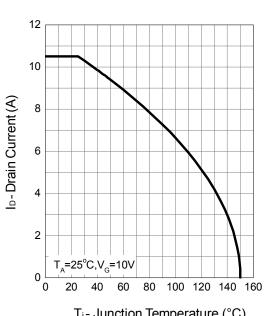


## **Typical Operating Characteristics**

# **Power Dissipation**

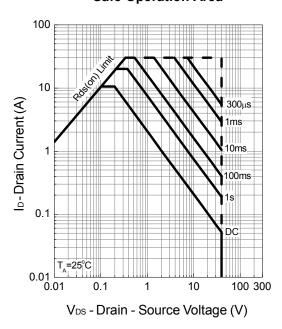


### **Drain Current**

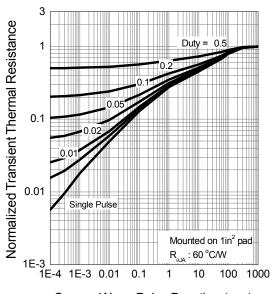


T<sub>j</sub>- Junction Temperature (°C)

## Safe Operation Area



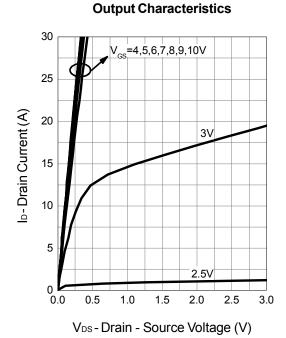
### **Thermal Transient Impedance**

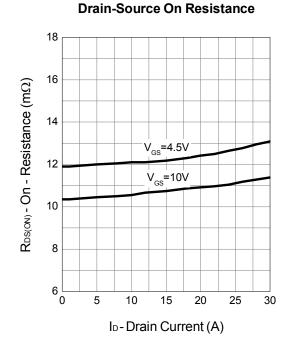


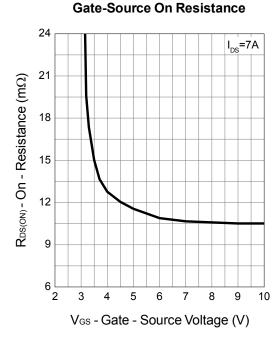
Square Wave Pulse Duration (sec)



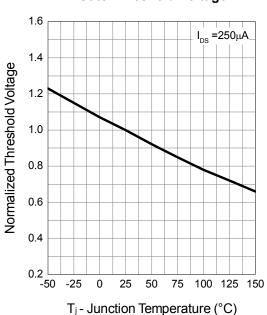
## **Typical Operating Characteristics (Cont.)**







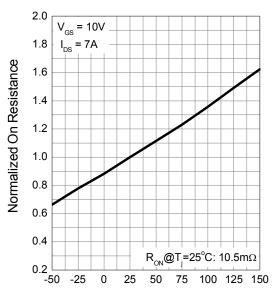
### **Gate Threshold Voltage**





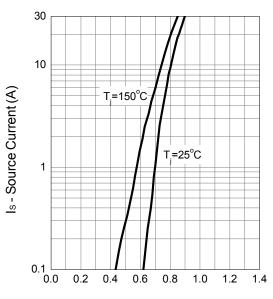
# **Typical Operating Characteristics (Cont.)**

## **Drain-Source On Resistance**



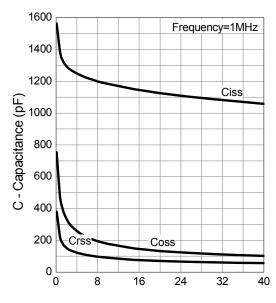
T<sub>j</sub> - Junction Temperature (°C)

### Source-Drain Diode Forward



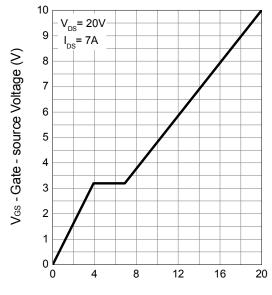
V<sub>SD</sub> - Source - Drain Voltage (V)

### Capacitance



V<sub>DS</sub> - Drain - Source Voltage (V)

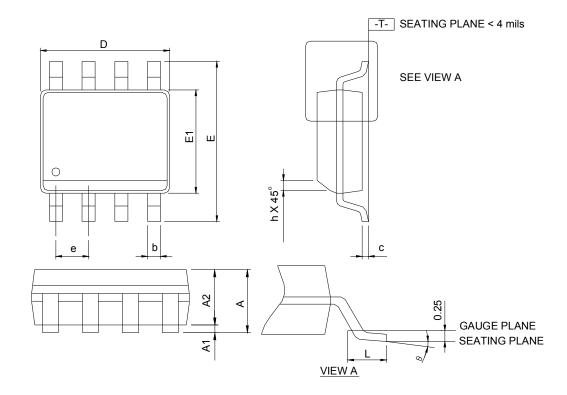
## **Gate Charge**



Q<sub>G</sub> - Gate Charge (nC)



# Package Information:SOP-8



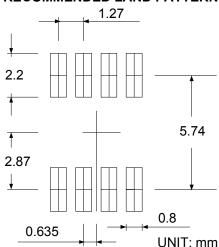
| Ş      | SOP-8       |      |           |       |  |
|--------|-------------|------|-----------|-------|--|
| SYMMOL | MILLIMETERS |      | INCHES    |       |  |
| P      | MIN.        | MAX. | MIN.      | MAX.  |  |
| Α      | -           | 1.75 | -         | 0.069 |  |
| A1     | 0.10        | 0.25 | 0.004     | 0.010 |  |
| A2     | 1.25        | -    | 0.049     | -     |  |
| b      | 0.31        | 0.51 | 0.012     | 0.020 |  |
| С      | 0.17        | 0.25 | 0.007     | 0.010 |  |
| D      | 4.80        | 5.00 | 0.189     | 0.197 |  |
| Е      | 5.80        | 6.20 | 0.228     | 0.244 |  |
| E1     | 3.80        | 4.00 | 0.150     | 0.157 |  |
| е      | 1.27 BSC    |      | 0.050 BSC |       |  |
| h      | 0.25        | 0.50 | 0.010     | 0.020 |  |
| L      | 0.40        | 1.27 | 0.016     | 0.050 |  |
| θ      | 0°          | 8°   | 0°        | 8°    |  |

|         |        | -       |        | -   |
|---------|--------|---------|--------|-----|
| Noto: 1 | Follow | IEDEC I | 10 012 | ۸ ۸ |

- 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.

  3. Dimension "E" does not include inter-lead flash or protrusions.
- Inter-lead flash and protrusions shall not exceed 10 mil per side.

## **RECOMMENDED LAND PATTERN**





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